CMHD3595

LOW LEAKAGE SILICON DIODE

SOD-123 CASE

Central™ Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMHD3595 is a Silicon Diode, manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high conductance applications requiring low leakage.
Marking Code is C95.

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	150	V
Peak Working Reverse Voltage	V_{RWM}	125	V
Average Forward Current	I_O	150	mA
Forward Steady-State Current	I_F	225	mA
Recurrent Peak Forward Current	i_f	600	mA
Peak Forward Surge Current (1.0s pulse)	I_{FSM}	500	mA
Peak Forward Surge Current (1.0μs pulse)	I_{FSM}	4.0	A
Power Dissipation	P_D	400	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	312.5	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
BV_R	I_R=100μA	150		V
I_R	V_R=125V		1.0	nA
I_R	V_R=125V, T_A=125°C		500	nA
I_R	V_R=125V, T_A=150°C		3.0	μA
I_R	V_R=30V, T_A=125°C		300	nA
V_F	I_F=1.0mA	0.54	0.69	V
V_F	I_F=5.0mA	0.62	0.77	V
V_F	I_F=10mA	0.65	0.80	V
V_F	I_F=50mA	0.75	0.88	V
V_F	I_F=100mA	0.79	0.92	V
V_F	I_F=200mA	0.83	1.00	V
C_T	V_R=0, f=1.0MHz		8.0	pF
t_{rr}	V_R=3.5V, I_f=10mA, R_L=1.0kΩ		3.0	μs

R2 (2-November 2001)

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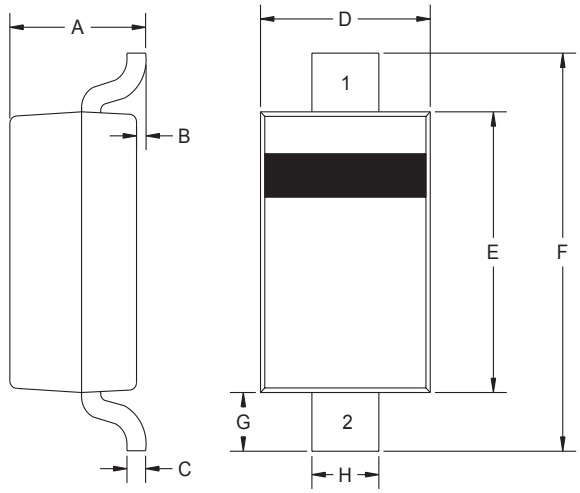
SOD-123 CASE - MECHANICAL OUTLINE



R3

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.037	0.053	0.95	1.35
B	-	0.005	-	0.12
C	-	0.008	-	0.20
D	0.055	0.071	1.40	1.80
E	0.098	0.112	2.50	2.84
F	0.140	0.154	3.55	3.90
G	0.010	-	0.25	-
H	0.020	0.028	0.50	0.70

SOD-123 (REV:R3)

LEAD CODE:

1) Cathode
2) Anode

MARKING CODE: C95

R2 (2-November 2001)